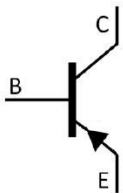


Silicon PNP transistor in a TO-92(R) Plastic Package.

High Voltage, Low Noise.

Low noise amplifier application.

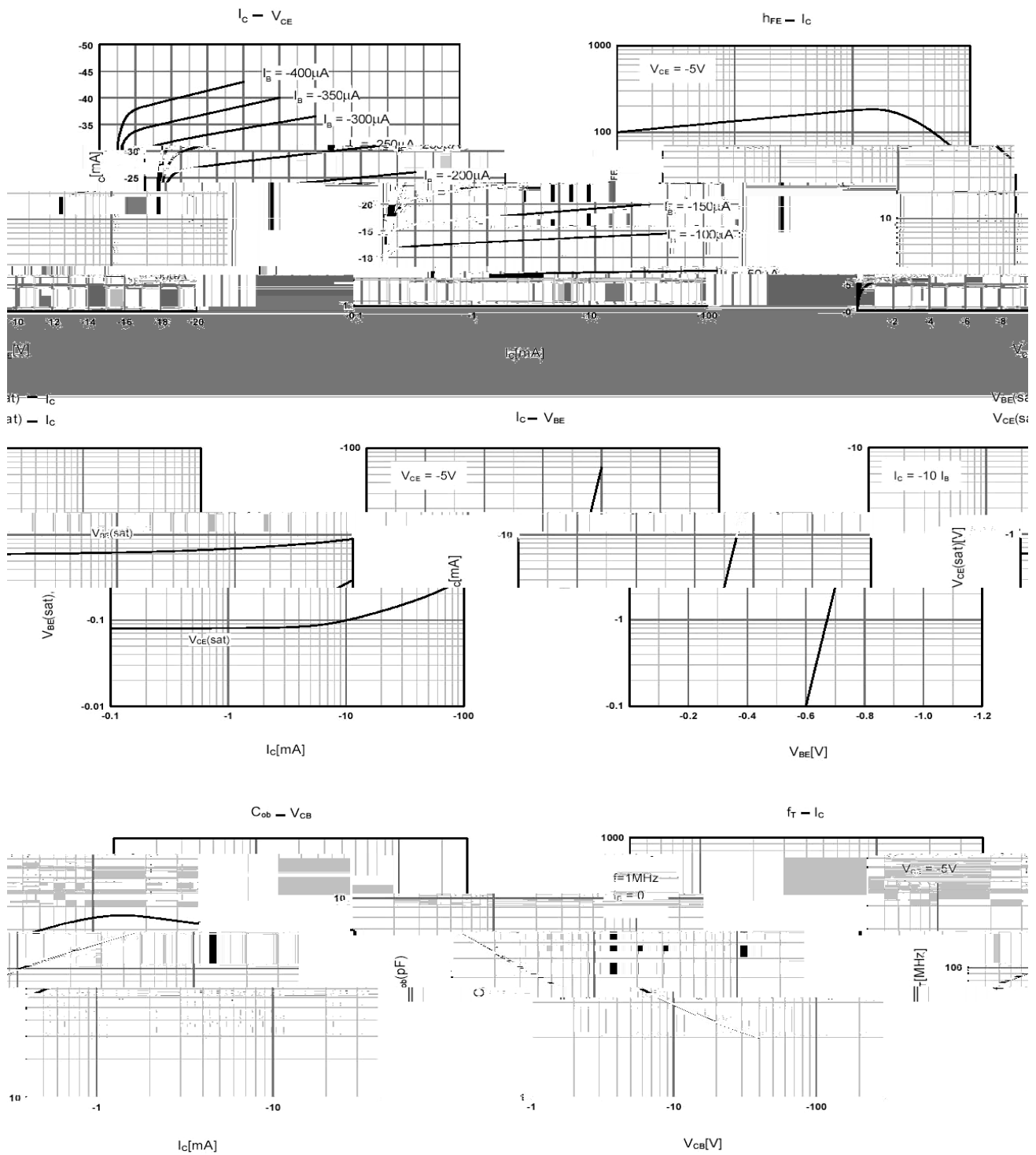


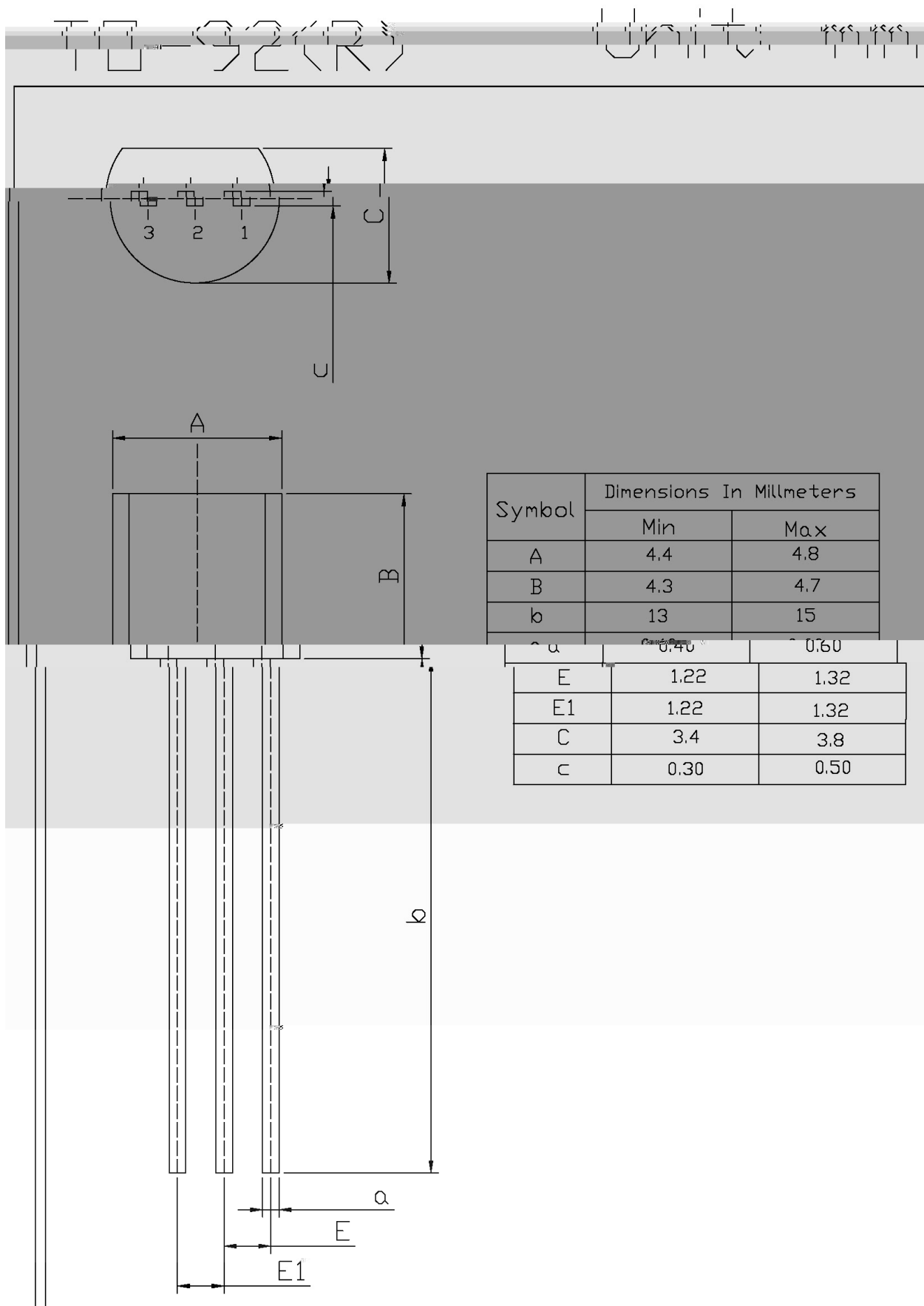
PIN1 Emitter PIN 2 Base PIN 3 Collector

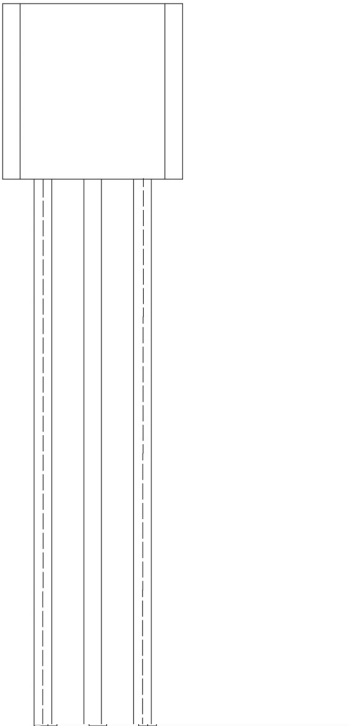
h_{FE} Classifications Symbol	A	B
h_{FE} Range	110~220	200~450

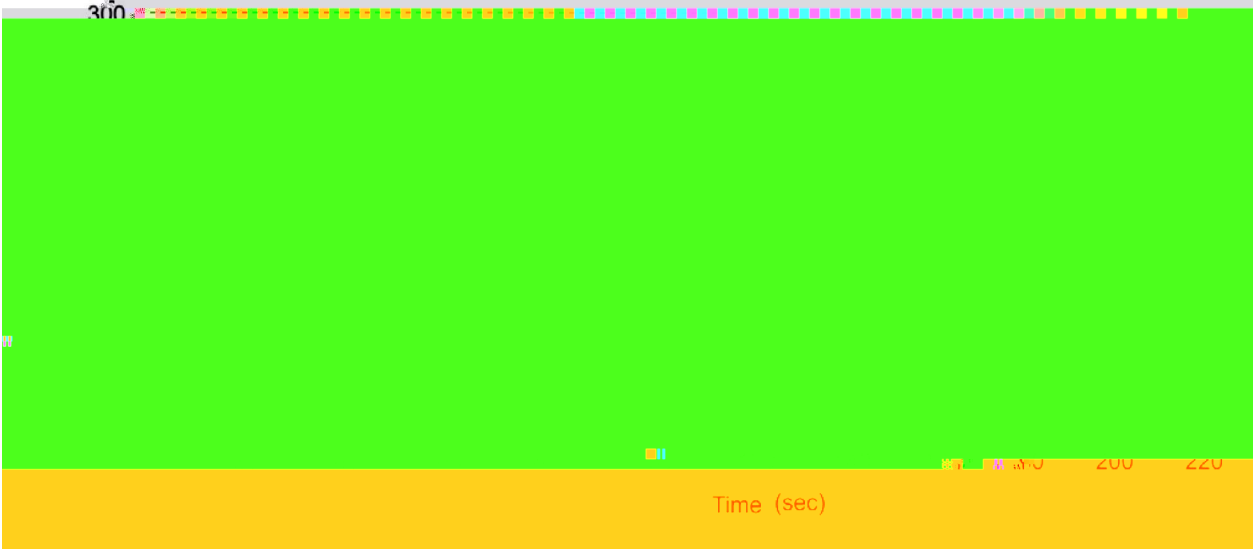
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-50	V
Collector to Emitter Voltage	V_{CEO}	-45	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-100	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55~150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-10mA$ $I_B=0$	-45			V
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=-10 A$ $I_E=0$	-50			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=-10 A$ $I_C=0$	-5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-30V$ $I_E=0$			-0.015	A
DC Current Gain	h_{FE}	$V_{CE}=-5.0V$ $I_C=-2.0mA$	110		450	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-100mA$ $I_B=-5.0mA$			-0.6	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=-100mA$ $I_B=-5.0mA$		-0.9		V
Base-Emitter Voltage	$V_{BE(on)}$	$V_{CE}=-5.0V$ $I_C=-2.0mA$	-0.55		-0.7	V
Transition Frequency	f_T	$V_{CE}=-5.0V$ $f=100MHz$ $I_C=-10mA$		300		MHz
Current Gain Bandwidth Product	C_{ob}	$V_{CB}=-10V$ $f=1.0MHz$ $I_E=0$			7.0	pF
Noise Figure	NF	$V_{CE}=-5.0V$ $R_g=10K$ $I_C=-200 A$ $f=1.0KHz$			4.0	dB









- Note:
- 1

25 150

60 90sec;

1.Preheating:25~150 , Time:60~90sec.
- 2

255 5

5 0.5sec;

2.Peak Temp.:255 5 , Duration:5 0.5sec.
- 3

2 10

/sec.

3. Cooling Speed: 2~10 /sec.

270 5

10 1 sec.

Temp.:270±5

Time:10±1 sec

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)		
	只 袋	袋 盒	只 盒	盒 箱	只 箱	袋	盒	箱

/ AMMO

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)	
	只 纸带	纸带 盒	纸带层 盒	盒 箱	只 箱	盒	箱
							小箱 , 大箱